PMEG3020CPAS

30 V, 2 A low VF dual MEGA Schottky barrier rectifier

20 January 2015 Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier in common cathode configuration with an integrated guard ring for stress protection, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current $I_{F(AV)} \leq 2$ A
- Reverse voltage $V_R \leq 30$ V
- Low forward voltage $V_F \leq 440$ mV
- Low reverse current
- Reduced Printed-Circuit-Board (PCB) area requirements
- Exposed heat sink (cathode pad) for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with visible and solderable side pads
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Free-wheeling application
- Reverse polarity protection
- Low power consumption application
- Battery chargers for mobile equipment
- LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per diode							
$I_{F(AV)}$	average forward current	δ = 0.5; f = 20 kHz; $T_{amb} \leq 75$ °C; square wave	[1]	-	-	2	A
		δ = 0.5; f = 20 kHz; $T_{sp} \leq 135$ °C; square wave		-	-	2	A

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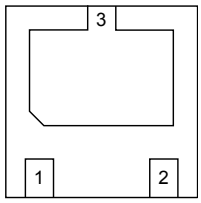
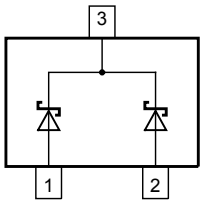
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_R	reverse voltage	T_j = 25 °C		-	-	30	V
Per diode							
V_F	forward voltage	I_F = 2 A; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_j = 25 °C; pulsed		-	410	440	mV
I_R	reverse current	V_R = 30 V; $t_p \leq 300$ µs; $\delta \leq 0.02$; T_j = 25 °C; pulsed		-	485	2000	µA

[1] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	anode diode 1	A1	 Transparent top view **DFN2020D-3 (SOT1061D)**	 *006aaa438*
2	anode diode 2	A2		
3	common cathode	K		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG3020CPAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG3020CPAS	CT

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V_R	reverse voltage	T_j = 25 °C		-	30	V
I_F	forward current	$T_{sp} \leq 130$ °C; $\delta = 1$		-	2.8	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; f = 20 kHz; $T_{amb} \leq 75$ °C; square wave	[1]	-	2	A
		$\delta = 0.5$; f = 20 kHz; $T_{sp} \leq 135$ °C; square wave		-	2	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ ms; $\delta \leq 0.25$		-	7	A
I_{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	9	A
Per device; one diode loaded						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[2]	-	500	mW
			[3]	-	960	mW
			[1]	-	1800	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

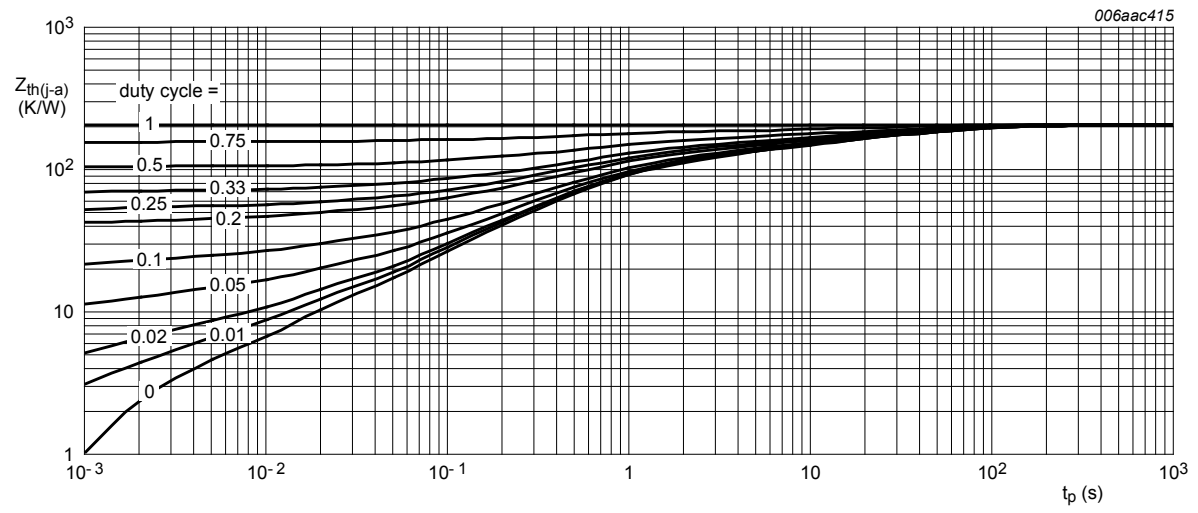
[1] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.

9. Thermal characteristics

Table 6. Thermal characteristics

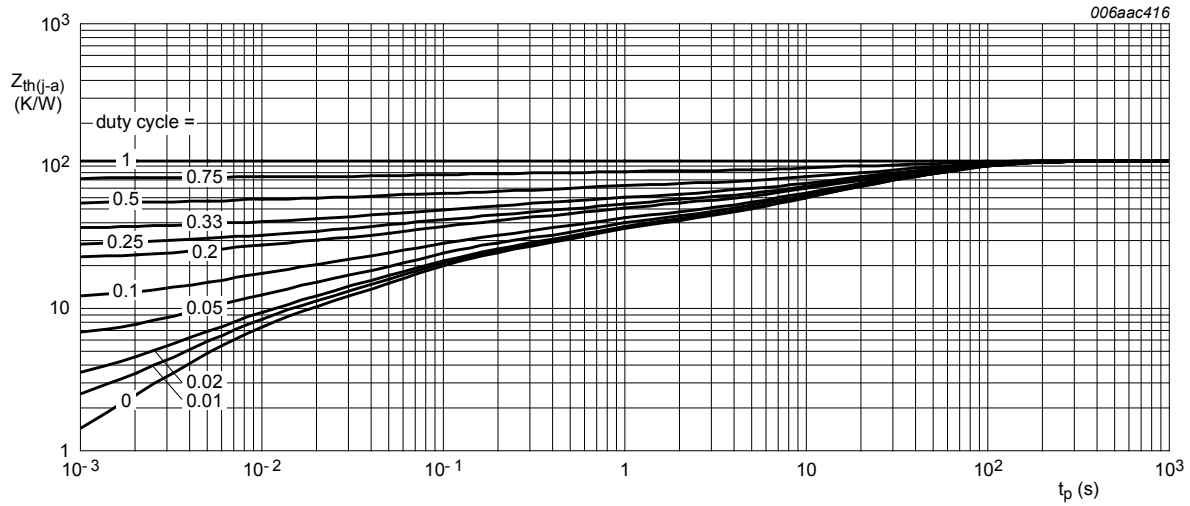
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per device; one diode loaded							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	250	K/W
			[1][3]	-	-	130	K/W
			[1][4]	-	-	70	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.
[4] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.
[5] Soldering point of cathode tab.



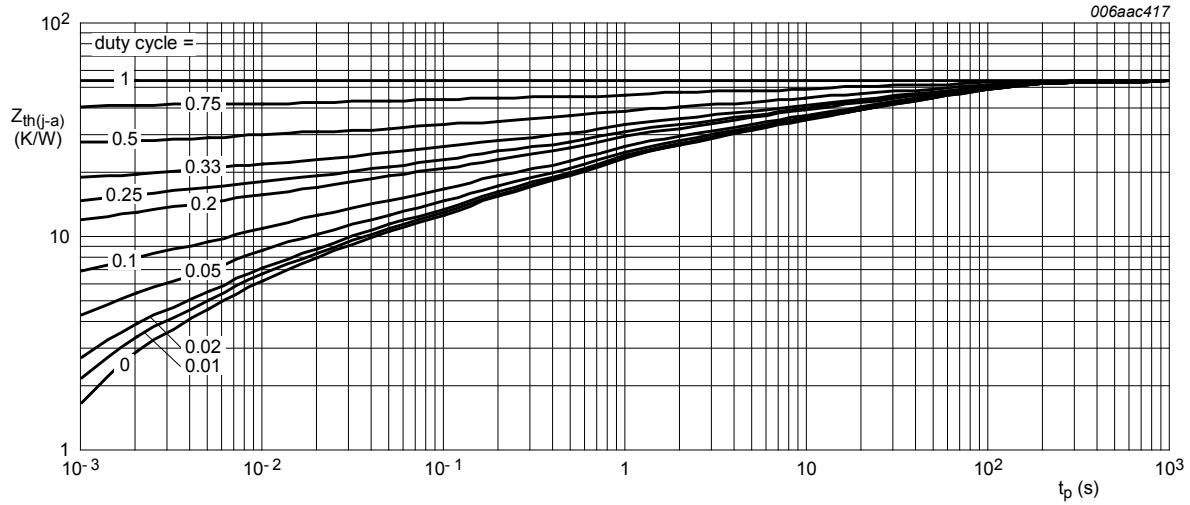
FR4 PCB, standard footprint

Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm^2

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



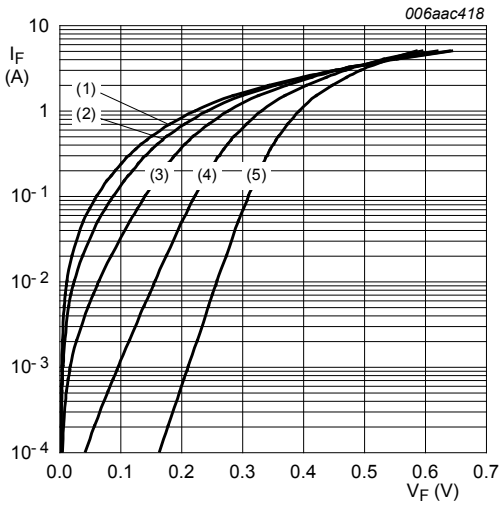
Ceramic PCB, Al_2O_3, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

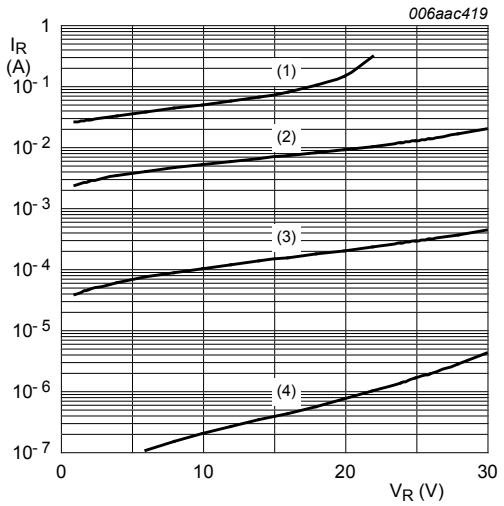
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per diode							
$V_{(BR)R}$	reverse breakdown voltage	I_R = 5 mA; T_j = 25 °C; t_p = 300 µs; δ = 0.02; pulsed		30	-	-	V
V_F	forward voltage	I_F = 100 mA; t_p ≤ 300 µs; δ ≤ 0.02; T_j = 25 °C; pulsed		-	220	-	mV
		I_F = 1 A; t_p ≤ 300 µs; δ ≤ 0.02; T_j = 25 °C; pulsed		-	335	370	mV
		I_F = 2 A; t_p ≤ 300 µs; δ ≤ 0.02; T_j = 25 °C; pulsed		-	410	440	mV
I_R	reverse current	V_R = 10 V; t_p ≤ 300 µs; δ ≤ 0.02; T_j = 25 °C; pulsed		-	120	-	µA
		V_R = 30 V; t_p ≤ 300 µs; δ ≤ 0.02; T_j = 25 °C; pulsed		-	485	2000	µA
C_d	diode capacitance	V_R = 1 V; f = 1 MHz; T_j = 25 °C		-	170	-	pF
		V_R = 10 V; f = 1 MHz; T_j = 25 °C		-	60	-	pF
t_{rr}	reverse recovery time	I_F = 0.5 A; I_R = 1 A; $I_{R(meas)}$ = 0.25 A; T_j = 25 °C		-	4	-	ns



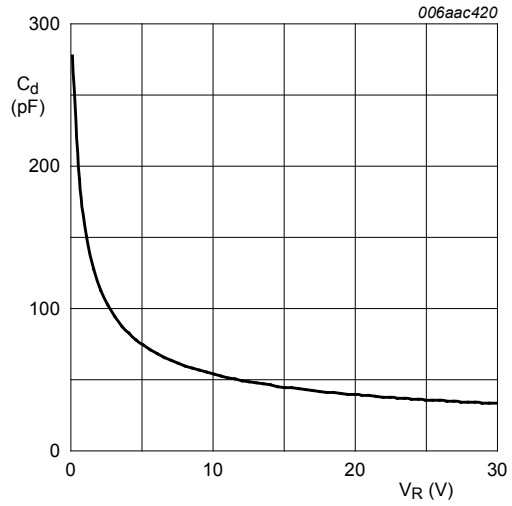
(1) T_j = 150 °C
(2) T_j = 125 °C
(3) T_j = 85 °C
(4) T_j = 25 °C
(5) T_j = −40 °C

Fig. 4. Forward current as a function of forward voltage; typical values



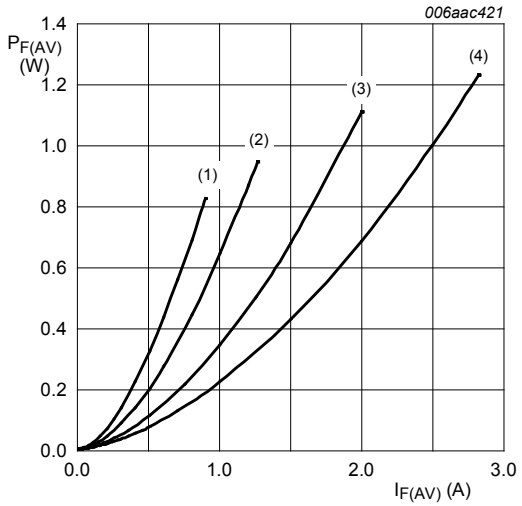
(1) T_j = 125 °C
(2) T_j = 85 °C
(3) T_j = 25 °C
(4) T_j = −40 °C

Fig. 5. Reverse current as a function of reverse voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



T_j = 150 °C

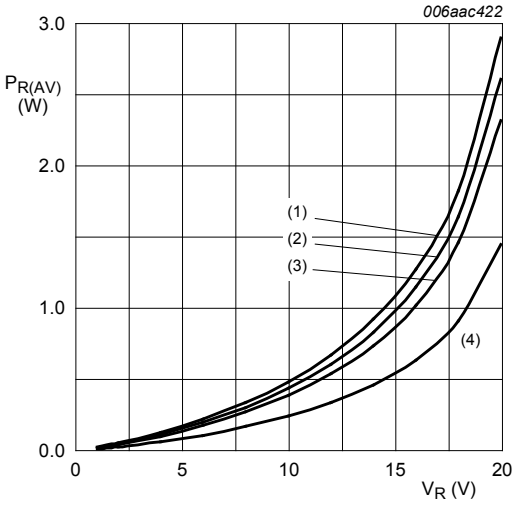
(1) δ = 0.1

(2) δ = 0.2

(3) δ = 0.5

(4) δ = 1

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



T_j = 125 °C

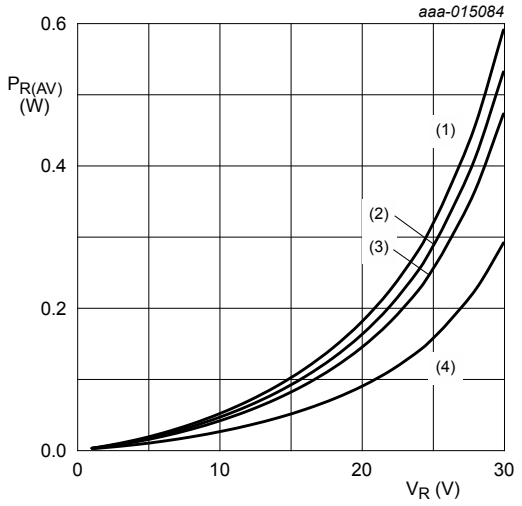
(1) δ = 1

(2) δ = 0.9

(3) δ = 0.8

(4) δ = 0.5

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



T_j = 85 °C

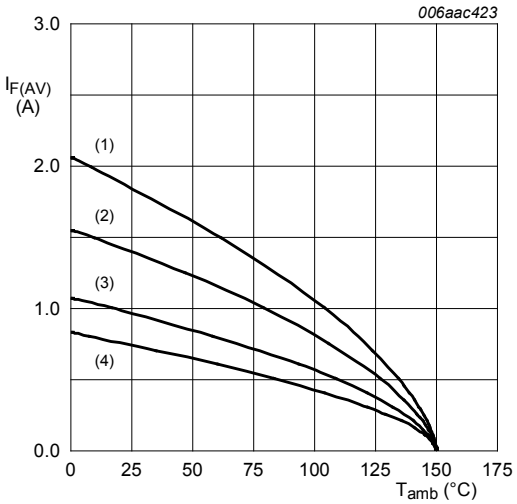
(1) δ = 1

(2) δ = 0.9

(3) δ = 0.8

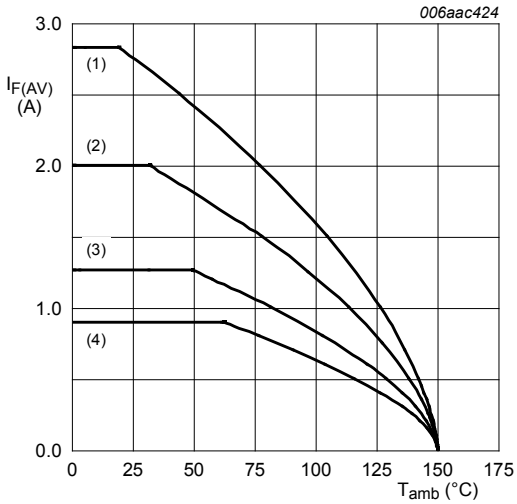
(4) δ = 0.5

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values



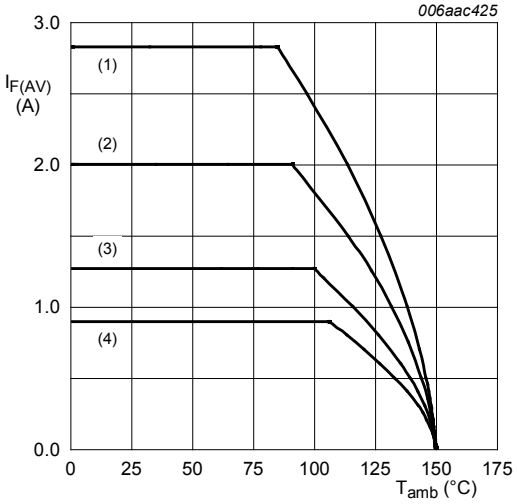
FR4 PCB, standard footprint
T_j = 150 °C
(1) δ = 1; DC
(2) δ = 0.5; f = 20 kHz
(3) δ = 0.2; f = 20 kHz
(4) δ = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



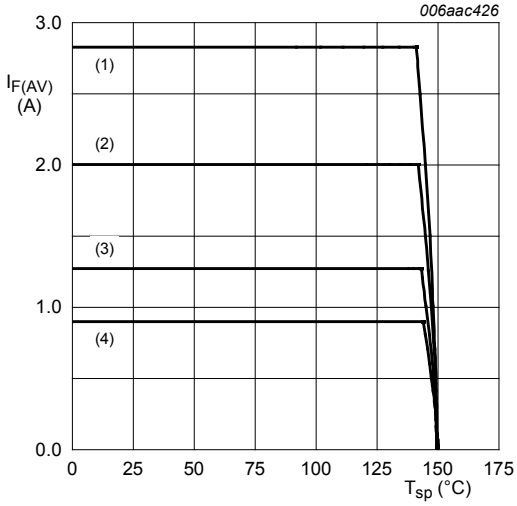
FR4 PCB, mounting pad for cathode 1 cm^2
T_j = 150 °C
(1) δ = 1; DC
(2) δ = 0.5; f = 20 kHz
(3) δ = 0.2; f = 20 kHz
(4) δ = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al_2O_3, standard footprint
T_j = 150 °C
(1) δ = 1; DC
(2) δ = 0.5; f = 20 kHz
(3) δ = 0.2; f = 20 kHz
(4) δ = 0.1; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



T_j = 150 °C
(1) δ = 1; DC
(2) δ = 0.5; f = 20 kHz
(3) δ = 0.2; f = 20 kHz
(4) δ = 0.1; f = 20 kHz

Fig. 13. Average forward current as a function of solder point temperature; typical values

11. Test information

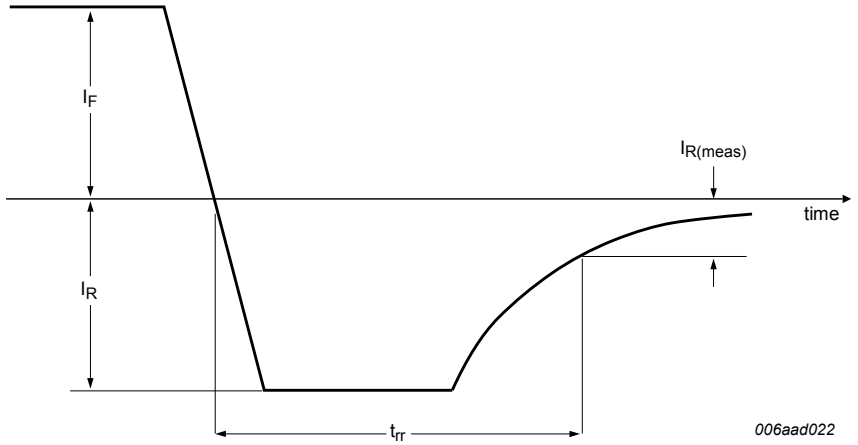


Fig. 14. Reverse recovery definition

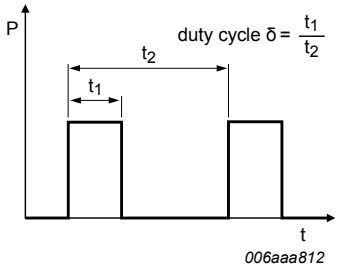


Fig. 15. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

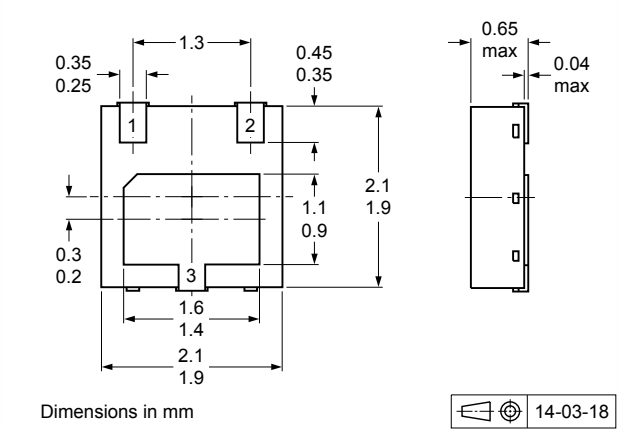


Fig. 16. Package outline DFN2020D-3 (SOT1061D)

13. Soldering

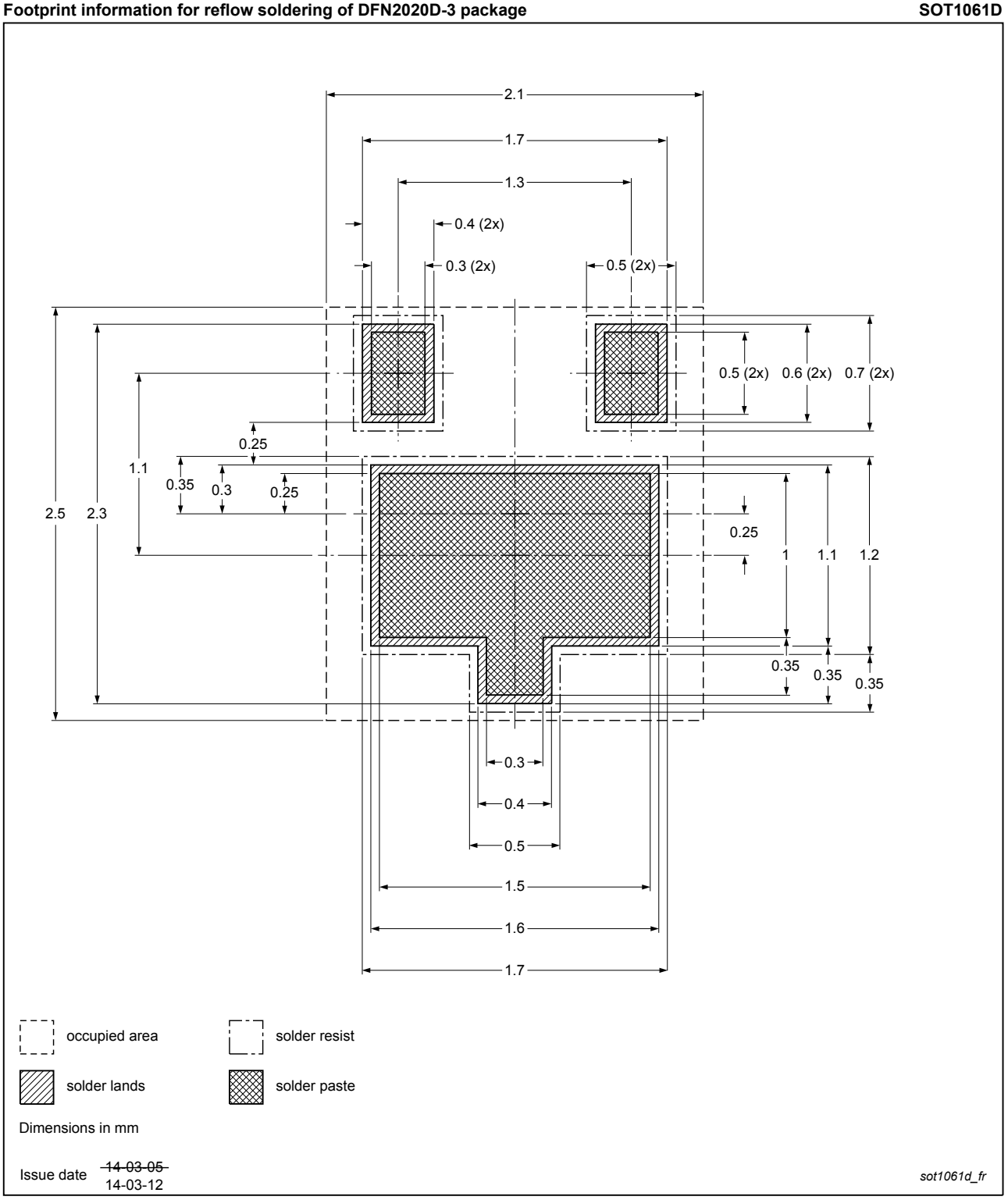


Fig. 17. Reflow soldering footprint for DFN2020D-3 (SOT1061D)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3020CPAS v.2	20150120	Product data sheet	-	PMEG3020CPAS v.1
Modifications:	• Changed data sheet status			
PMEG3020CPAS v.1	20141210	Preliminary data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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